

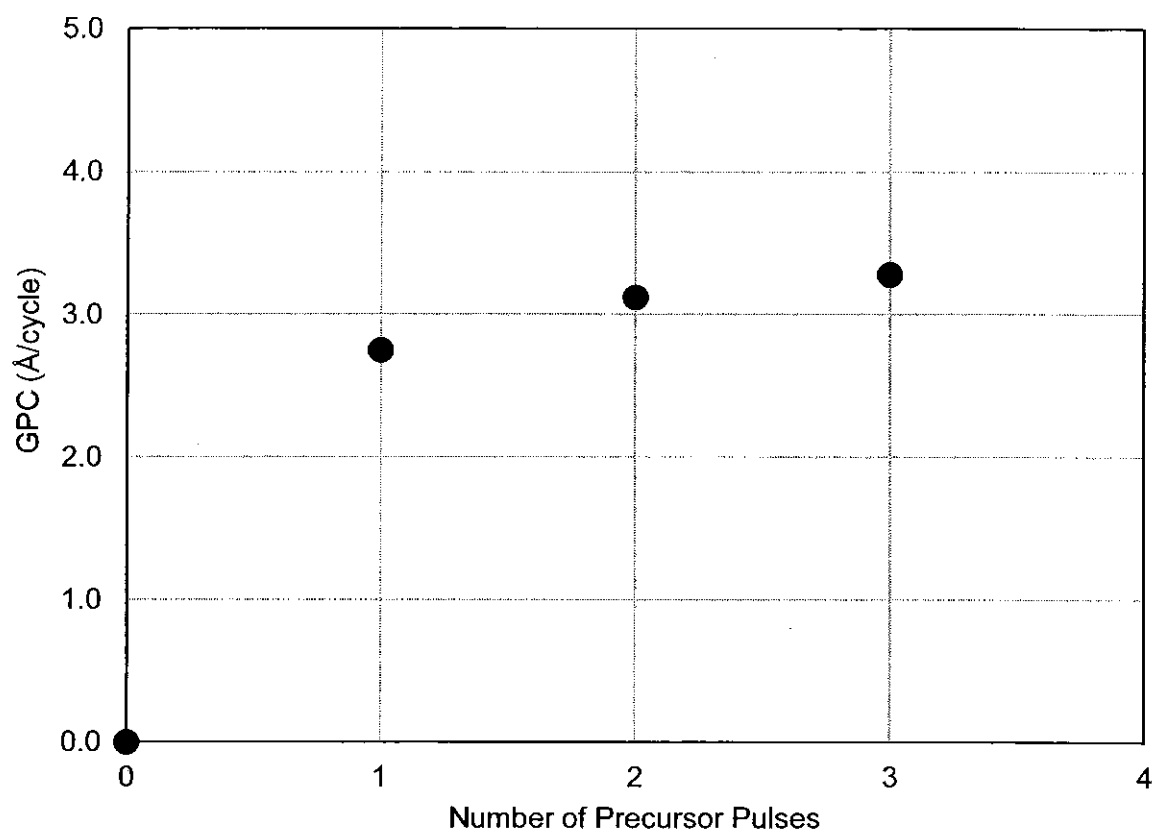


Figure 1. Thermal ALD GPC versus number of precursor pulses of 2-dimethylamino-2,4,6,8-tetramethylcyclotetrasiloxane with ozone process at 300 °C.

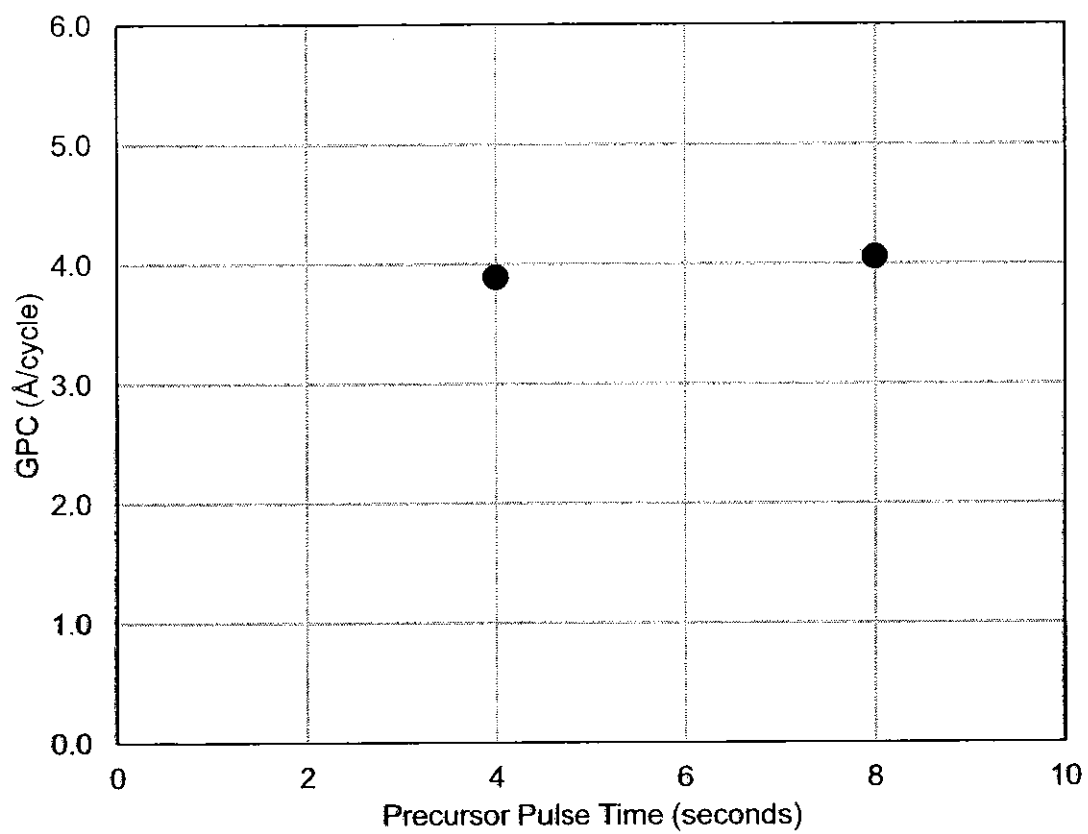


Figure 2. PEALD silicon oxide deposition GPC versus precursor pulse time with 2-dimethylamino-2,4,6,8- tetramethylcyclotetrasiloxane

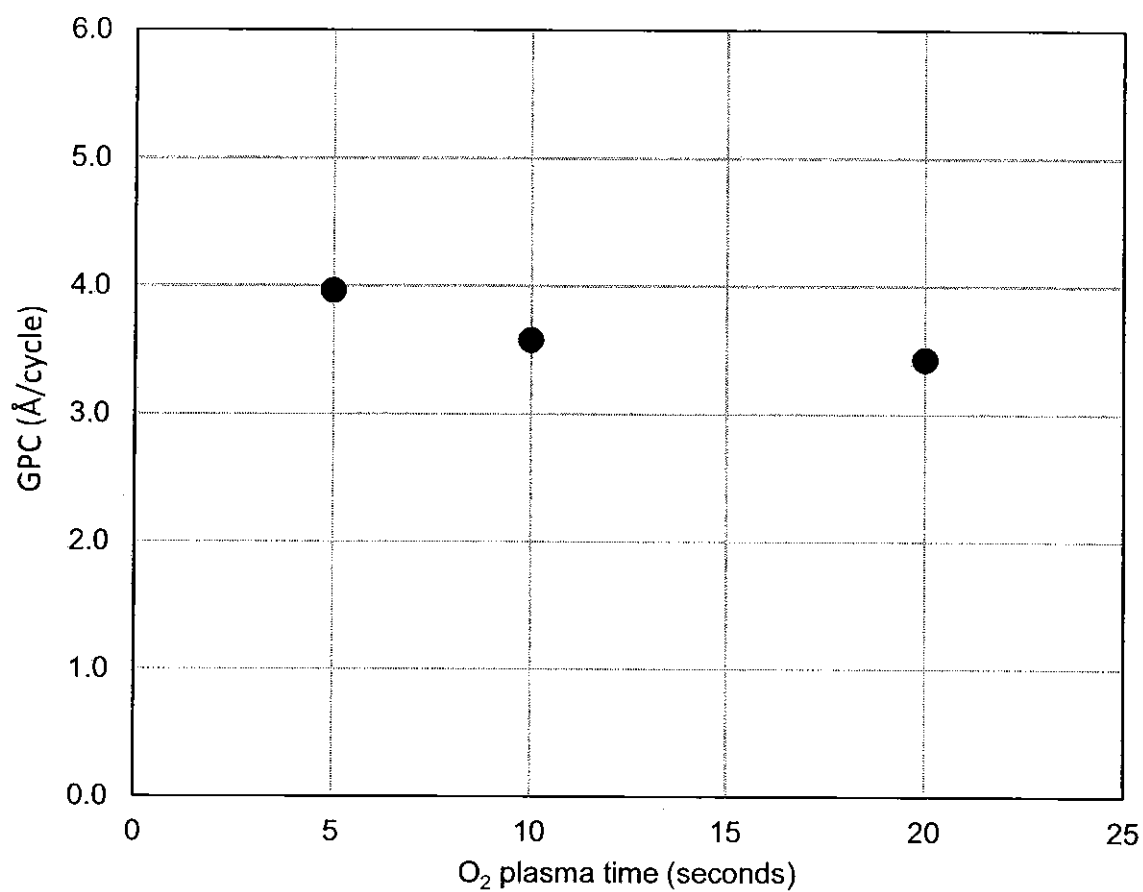


Figure 3. PEALD silicon oxide deposition GPC versus O₂ plasma exposure time with 2-dimethylamino-2,4,6,8- tetramethylcyclotetrasiloxane

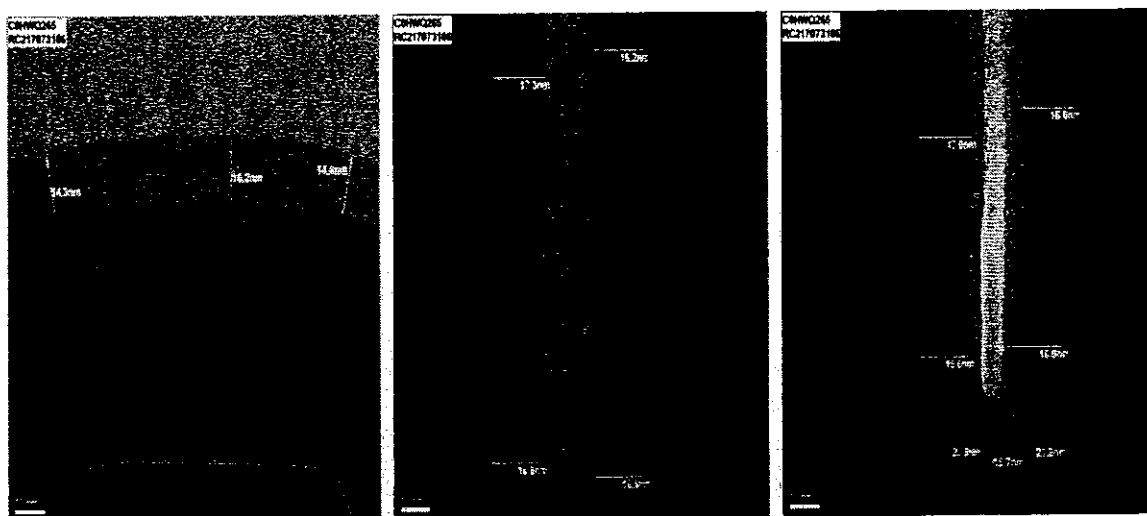


Figure 4. TEM image of silicon oxide film deposited by 2-dimethylamino-2,4,6,8-tetramethylcyclotetrasiloxane in laminar flow reactor

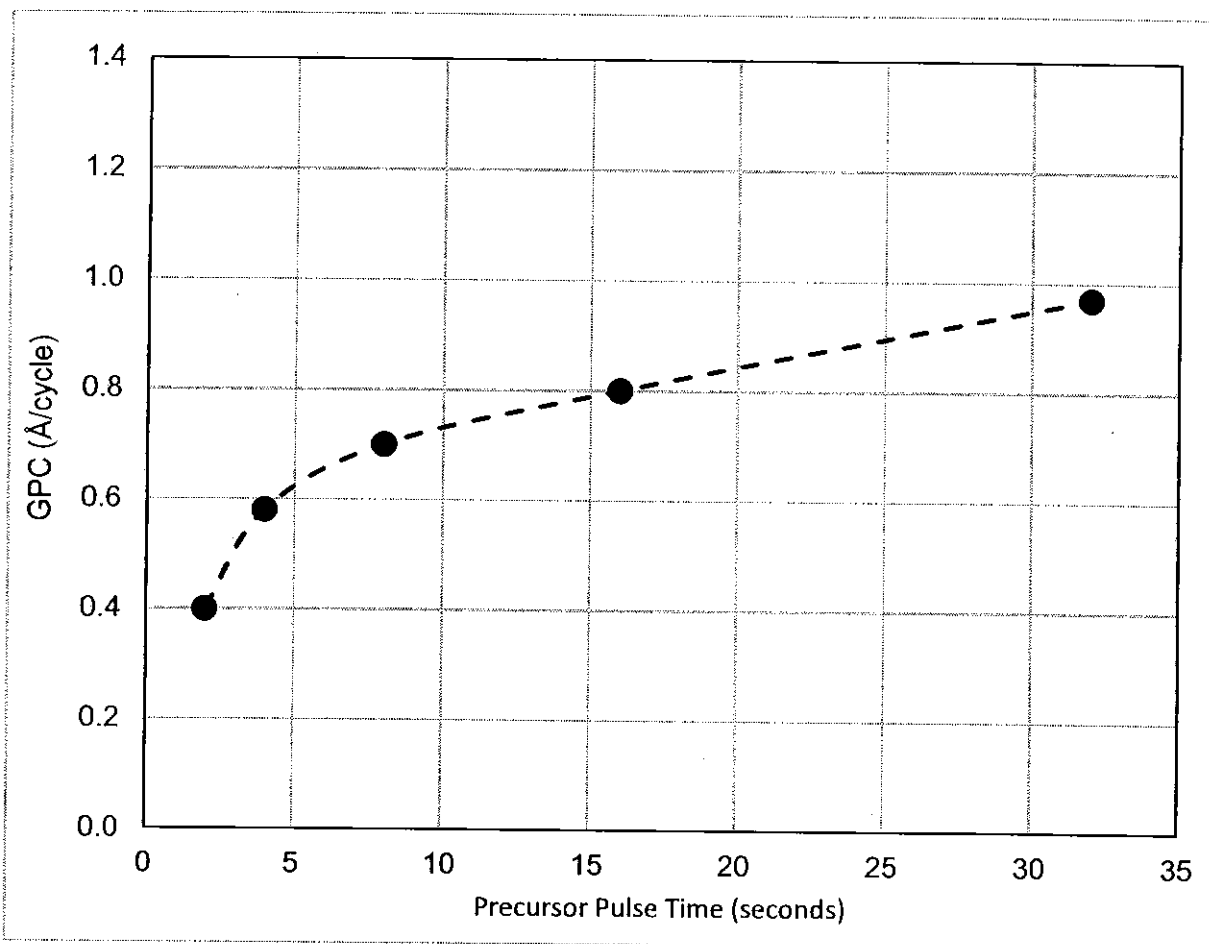


Figure 5. PEALD silicon oxide deposition GPC versus precursor pulse time with TMCTS in Showerhead Chamber.



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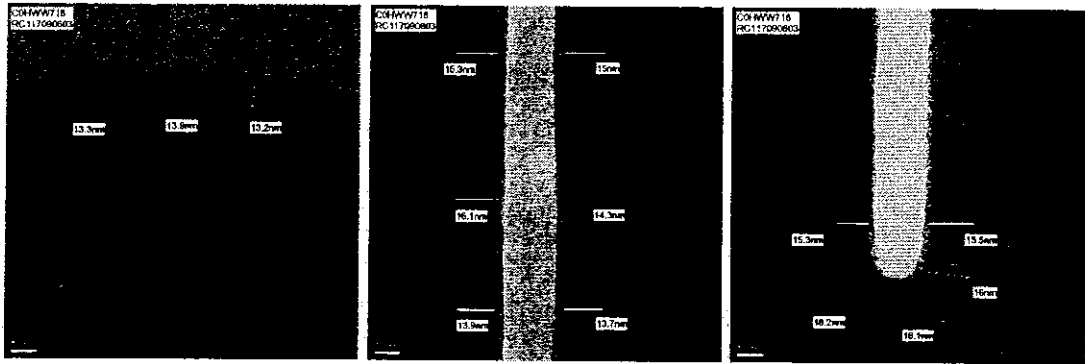


Figure 7. TEM image of silicon oxide film deposited by 2-dimethylamino-2,4,6,8-tetramethylcyclotetrasiloxane in shower head chamber.